(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
11 March 2004 (11.03.2004)

PCT

(10) International Publication Number
WO 2004/021440 A1

(51) International Patent Classification[7]: H01L 27/06, 27/08, 21/02

(21) International Application Number:
PCT/US2003/027367

(22) International Filing Date: 29 August 2003 (29.08.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
102 40 423.2 2 September 2002 (02.09.2002) DE
10/403,481 31 March 2003 (31.03.2003) US

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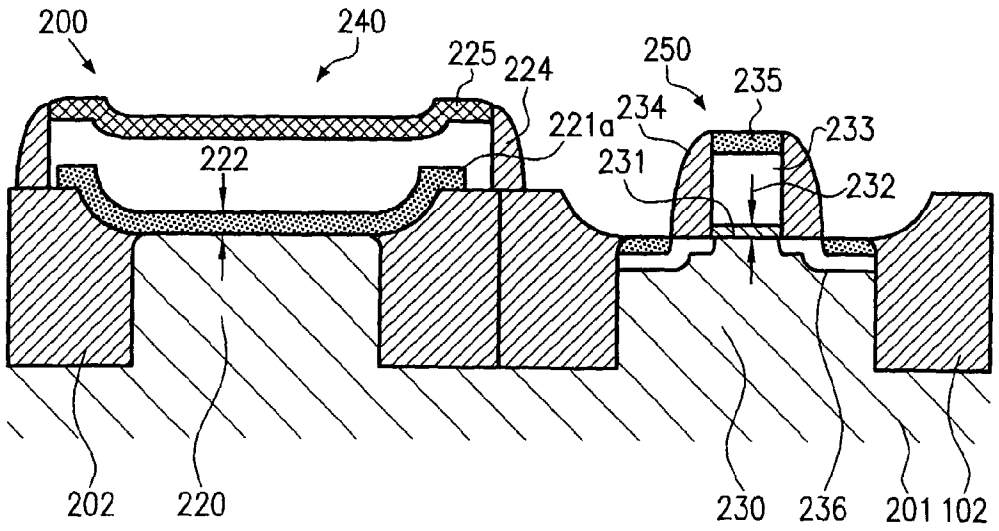
(81) Designated States *(national)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States *(regional)*: ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*

[Continued on next page]

(54) Title: SEMICONDUCTOR DEVICE INCLUDING A FIELD EFFECT TRANSISTOR AND A PASSIVE CAPACITOR HAVING REDUCED LEAKAGE CURRENT AND AN IMPROVED CAPACITANCE PER UNIT AREA



(57) Abstract: A semiconductor device comprises a field effect transistor (250) and a passive capacitor (240), wherein the dielectric layer (221a) of the capacitor (240) is comprised of a high-k material, whereas the gate insulation layer (231) of the field effect transistor (250) is formed of an ultra thin oxide layer or oxynitride layer so as to provide for superior carrier mobility at the interface between the gate insulation layer and the underlying channel region. Since carrier mobility in the capacitor is not of great importance, the high-k material allows the provision of high capacitance per unit area while featuring a thickness sufficient to effectively reduce leakage current.

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— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

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